MOSFETs Silicon N-channel MOS (U-MOSIX-H)

TPH2R003PL

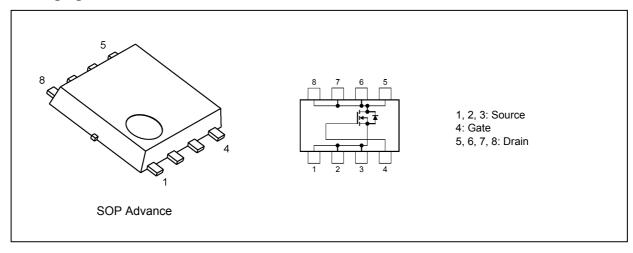
1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 22 \text{ nC}$ (typ.)
- (3) Small output charge: $Q_{oss} = 41 \text{ nC}$ (typ.)
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 1.3 \text{ m}\Omega$ (typ.) (V_{GS} = 10 V)
- (5) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 30 \ V)$
- (6) Enhancement mode: V_{th} = 1.1 to 2.1 V (V_{DS} = 10 V, I_D = 0.5 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characteris	Symbol	Rating	Unit		
Drain-source voltage			V _{DSS}	30	V
Gate-source voltage		(Note 1)	V _{GSS}	±20	
Drain current (DC)	(T _c = 25 °C)	(Note 2)	Ι _D	100	Α
Drain current (DC)	(Silicon limit)	(Note 2), (Note 3)	Ι _D	180	
Drain current (pulsed)	(t = 100 µs)	(Note 2)	I _{DP}	200	
Power dissipation	(T _c = 25 °C)		PD	116	W
Power dissipation		(Note 4)	PD	1.8	
Power dissipation		(Note 5)	PD	0.83	
Single-pulse avalanche energy		(Note 6)	E _{AS}	92	mJ
Single-pulse avalanche current		(Note 6)	I _{AS}	100	А
Channel temperature			T _{ch}	175	°C
Storage temperature			T _{stg}	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	(T _c = 25 °C)		R _{th(ch-c)}	1.29	°C/W
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 4)	R _{th(ch-a)}	83	
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 5)	R _{th(ch-a)}	180	

Note 1: +20 V/-16 V ensured at DC condition.

-20 V ensured at pulse condition (duty 5 %).

Note 2: Ensure that the channel temperature does not exceed 175 °C.

Note 3: Limited 100 A by package capability.

Note 4: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 5: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 6: V_{DD} = 24 V, T_{ch} = 25 °C (initial), L = 7.1 μ H, I_{AS} = 100 A

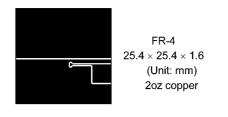
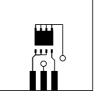
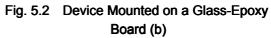


Fig. 5.1 Device Mounted on a Glass-Epoxy

Board (a)



FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2oz copper



Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	_	_	±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	30	—	_	V
Drain-source breakdown voltage (Note 7)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	15	_	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.5 mA	1.1		2.1	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 4.5 V, I _D = 50 A		1.7	2.6	mΩ
		V _{GS} = 10 V, I _D = 50 A	_	1.3	2.0	

Note 7: If a reverse bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	_	4930	6410	pF
Reverse transfer capacitance	C _{rss}		_	135	245	
Output capacitance	C _{oss}		_	1455	_	
Gate resistance	r _g	—	—	1.0	1.5	Ω
Switching time (rise time)	t _r	See Figure 6.2.1	_	8.2	—	ns
Switching time (turn-on time)	t _{on}		_	23	_	
Switching time (fall time)	t _f]	_	8.6	_	
Switching time (turn-off time)	t _{off}			49	_	

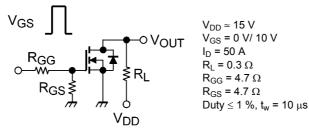


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

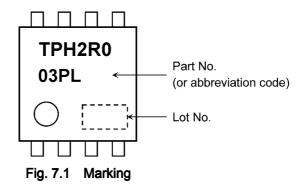
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Qg	$V_{DD} \approx 15 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 50 \text{ A}$	_	86	_	nC
gate-drain)		$V_{DD} \approx 15 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 50 \text{ A}$	_	41	_	
Gate-source charge 1	Q _{gs1}	$V_{DD} \approx 15 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 50 \text{ A}$	_	19	_	
Gate-drain charge	Q _{gd}		_	12	_	
Gate switch charge	Q _{SW}		_	22	_	
Output charge	Q _{oss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	_	41	_	

6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

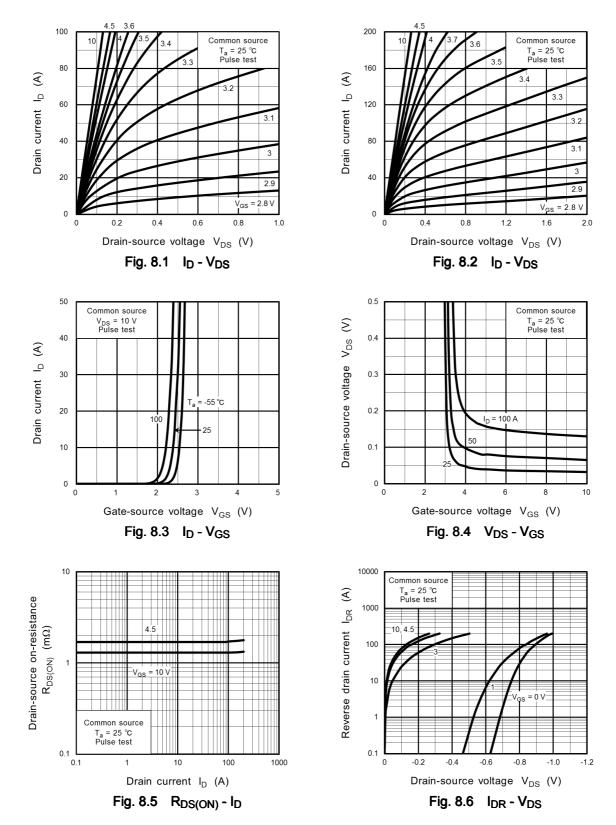
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 8)	I _{DRP}	(t = 100 μs)	_	_	200	А
Diode forward voltage		V _{DSF}	I _{DR} = 100 A, V _{GS} = 0 V	_	—	-1.2	V
Reverse recovery time			V _R = 15 V, I _{DR} = 25 A,	_	44	_	ns
Reverse recovery charge		Q _{rr}	V _{GS} = 0 V, -dI _{DR} /dt = 100 A/μs		43		nC

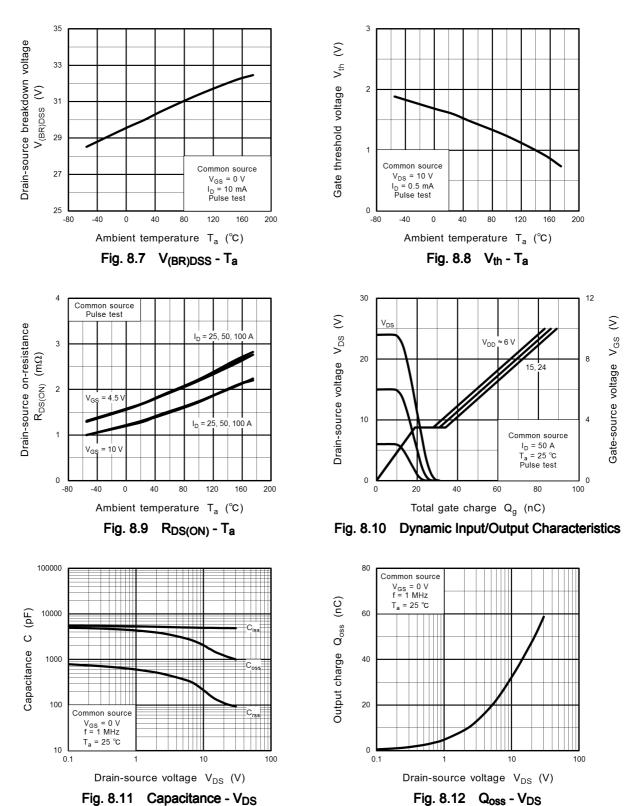
Note 8: Ensure that the channel temperature does not exceed 175 °C.

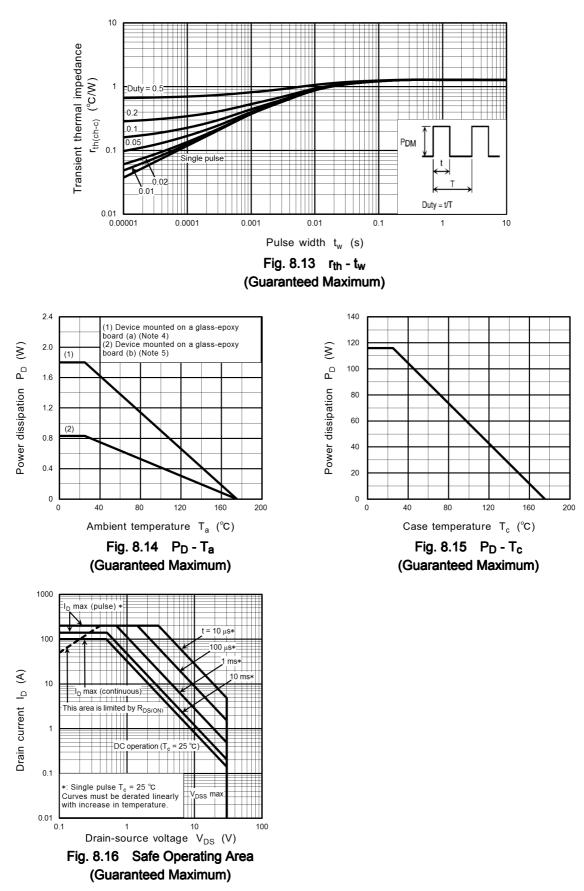
7. Marking



8. Characteristics Curves (Note)







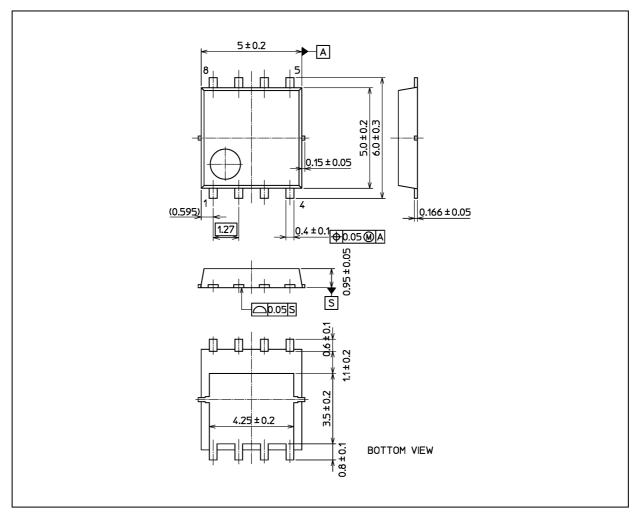
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



TPH2R003PL

Package Dimensions

Unit: mm



Weight: 0.069 g (typ.)

TOSHIBA: 2-5Q1S

Nickname: SOP Advance

Package Name(s)

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